

IRHNJ57Z30 (JANSR2N7479U3)

PD-93751H

Radiation Hardened Power MOSFET Surface Mount (SMD-0.5) 30V, 22A, N-channel, R5 Technology

Features

- Single event effect (SEE) hardened
- Ultra low $R_{DS(on)}$
- Low total gate charge
- Simple drive requirements
- Hermetically sealed
- Light weight
- Ceramic package
- Surface Mount
- ESD rating: Class 1C per MIL-STD-750, Method 1020

Product Summary

- **BV_{DSS} :** 30V
- **I_D :** 22A
- **$R_{DS(on),max}$:** 20m Ω
- **$Q_{G,max}$:** 65nC
- **REF:** MIL-PRF-19500/703



Potential Applications

- Synchronous rectification
- Point of load converter
- Active ORing circuits

Product Validation

Qualified to JANS screening flow according to MIL-PRF-19500 for space applications

Description

IR HiRel R5 technology provides high performance power MOSFETs for space applications. This technology has over a decade of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low $R_{DS(on)}$ and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well-established advantages of MOSFETs such as voltage control, fast switching and temperature stability of electrical parameters.

Ordering Information

Table 1 Ordering options

Part number	Package	Screening Level	TID Level
IRHNJ57Z30	SMD-0.5	COTS	100 krad(Si)
JANSR2N7479U3	SMD-0.5	JANS	100 krad(Si)
IRHNJ53Z30	SMD-0.5	COTS	300 krad(Si)
JANSF2N7479U3	SMD-0.5	JANS	300 krad(Si)
IRHNJ54Z30	SMD-0.5	COTS	500 krad(Si)
JANSG2N7479U3	SMD-0.5	JANS	500 krad(Si)

IRHNJ57Z30 (JANSR2N7479U3)

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Table of contents

Table of contents

Features	1
Potential Applications.....	1
Product Validation.....	1
Description	1
Ordering Information.....	1
Table of contents.....	2
1 Absolute Maximum Ratings	3
2 Device Characteristics	4
2.1 Electrical Characteristics (Pre-Irradiation).....	4
2.2 Source-Drain Diode Ratings and Characteristics (Pre-Irradiation)	5
2.3 Thermal Characteristics	5
2.4 Radiation Characteristics.....	5
2.4.1 Electrical Characteristics — Post Total Dose Irradiation	5
2.4.2 Single Event Effects — Safe Operating Area	6
3 Electrical Characteristics Curves (Pre-irradiation)	7
4 Test Circuits (Pre-irradiation)	10
5 Package Outline.....	11
Revision history.....	12

Absolute Maximum Ratings

1 Absolute Maximum Ratings

Table 2 Absolute Maximum Ratings (Pre-Irradiation)

Symbol	Parameter	Value	Unit
$I_{D1} @ V_{GS} = 12V, T_C = 25^{\circ}C$	Continuous Drain Current	22*	A
$I_{D2} @ V_{GS} = 12V, T_C = 100^{\circ}C$	Continuous Drain Current	22*	A
$I_{DM} @ T_C = 25^{\circ}C$	Pulsed Drain Current ¹	88	A
$P_D @ T_C = 25^{\circ}C$	Maximum Power Dissipation	75	W
	Linear Derating Factor	0.6	W/ $^{\circ}C$
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ²	155	mJ
I_{AR}	Avalanche Current ¹	22	A
E_{AR}	Repetitive Avalanche Energy ¹	7.5	mJ
dv/dt	Peak Diode Reverse Recovery ³	1.7	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	$^{\circ}C$
	Lead Temperature	300 (for 5 sec)	
	Weight	1.0 (Typical)	

* Current is limited by package

¹ Repetitive Rating; Pulse width limited by maximum junction temperature.² $V_{DD} = 15V$, starting $T_J = 25^{\circ}C$, $L = 0.64mH$, Peak $I_L = 22A$, $V_{GS} = 12V$ ³ $I_{SD} \leq 22A$, $di/dt \leq 54A/\mu s$, $V_{DD} \leq 30V$, $T_J \leq 150^{\circ}C$

Device Characteristics

2 Device Characteristics

2.1 Electrical Characteristics (Pre-Irradiation)

Table 3 Static and Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 1.0mA$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.028	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1.0mA$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	20	m Ω	$V_{GS} = 12V, I_{D2} = 22A^1$
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 1mA$
G_{fs}	Forward Transconductance	16	—	—	S	$V_{DS} = 15V, I_{D2} = 22A^1$
I_{DSS}	Zero Gate Voltage Drain Current	—	—	10	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	25		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Leakage Reverse	—	—	-100		$V_{GS} = -20V$
Q_G	Total Gate Charge	—	—	65	nC	$I_{D1} = 22A$
Q_{GS}	Gate-to-Source Charge	—	—	20		$V_{DS} = 15V$
Q_{GD}	Gate-to-Drain ('Miller') Charge	—	—	10		$V_{GS} = 12V$
$t_{d(on)}$	Turn-On Delay Time	—	—	25	ns	$I_{D1} = 22A^{**}$ $V_{DD} = 15V$ $R_G = 7.5\Omega$ $V_{GS} = 12V$
t_r	Rise Time	—	—	100		
$t_{d(off)}$	Turn-Off Delay Time	—	—	35		
t_f	Fall Time	—	—	30		
$L_s + L_D$	Total Inductance	—	4.0	—	nH	Measured from center of Drain pad to center of Source pad
C_{iss}	Input Capacitance	—	2054	—	pF	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1.0MHz$
C_{oss}	Output Capacitance	—	936	—		
C_{rss}	Reverse Transfer Capacitance	—	33	—		

** Switching speed maximum limits are based on manufacturing test equipment and capability.

¹ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$

Device Characteristics

2.2 Source-Drain Diode Ratings and Characteristics (Pre-Irradiation)

Table 4 Source-Drain Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	22	A	
I _{SM}	Pulsed Source Current (Body Diode) ¹	—	—	88	A	
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _J = 25°C, I _S = 22A, V _{GS} = 0V ²
t _{rr}	Reverse Recovery Time	—	—	102	ns	T _J = 25°C, I _F = 22A, V _{DD} ≤ 25V di/dt = 100A/μs
Q _{rr}	Reverse Recovery Charge	—	129	—	nC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

2.3 Thermal Characteristics

Table 5 Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction-to-Case	—	—	1.67	$^\circ\text{C}/\text{W}$
$R_{\theta PCB}$	Junction-to-PC Board (soldered to 1inch square cu clad board)	—	6.9	—	

2.4 Radiation Characteristics

IR HiRel radiation hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR HiRel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 3 and 4) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

2.4.1 Electrical Characteristics — Post Total Dose Irradiation

Table 6 Electrical Characteristics @ $T_J = 25^\circ\text{C}$, Post Total Dose Irradiation ^{3, 4}

Symbol	Parameter	Up to 500 krad (Si) ⁵		Unit	Test Conditions
		Min.	Max.		
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	—	V	$V_{GS} = 0\text{V}$, $I_D = 1.0\text{mA}$
$V_{GS(th)}$	Gate Threshold Voltage	2.0	4.0	V	$V_{DS} = V_{GS}$, $I_D = 1.0\text{mA}$
I_{GSS}	Gate-to-Source Leakage Forward	—	100	nA	$V_{GS} = 20\text{V}$
	Gate-to-Source Leakage Reverse	—	-100		$V_{GS} = -20\text{V}$
I_{DSS}	Zero Gate Voltage Drain Current	—	10	μA	$V_{DS} = 24\text{V}$, $V_{GS} = 0\text{V}$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance (TO-3) ²	—	24	$\text{m}\Omega$	$V_{GS} = 12\text{V}$, $I_{D2} = 22\text{A}$
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance (SMD-0.5) ²	—	20	$\text{m}\Omega$	$V_{GS} = 12\text{V}$, $I_{D2} = 22\text{A}$
V_{SD}	Diode Forward Voltage	—	1.2	V	$V_{GS} = 0\text{V}$, $I_F = 22\text{A}$

¹ Repetitive Rating; Pulse width limited by maximum junction temperature.

² Pulse width $\leq 300\text{ }\mu\text{s}$; Duty Cycle $\leq 2\%$

³ Total Dose Irradiation with V_{GS} Bias. $V_{GS} = 12\text{V}$ applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, Method 1019, condition A.

⁴ Total Dose Irradiation with V_{DS} Bias. $V_{DS} = 24\text{V}$ applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, Method 1019, condition A.

⁵ Part numbers IRHNJ57Z30 (JANSR2N7479U3), IRHNJ53Z30 (JANSF2N7479U3) and IRHNJ54Z30 (JANSF2N7479U3)

IRHNJ57Z30 (JANSR2N7479U3)

Radiation Hardened Power MOSFET Surface Mount (SMD-0.5)

Device Characteristics

2.4.2 Single Event Effects — Safe Operating Area

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. 1 and Table 7.

Table 7 Typical Single Event Effects Safe Operating Area

LET (MeV·cm ² /mg)	Energy (MeV)	Range (μm)	V _{DS} (V)				
			V _{GS} = 0V	V _{GS} = -5V	V _{GS} = -10V	V _{GS} = -15V	V _{GS} = -20V
38 ± 5%	300 ± 7.5%	38 ± 7.5%	30	30	30	22.5	15
61 ± 5%	330 ± 7.5%	31 ± 10%	25	25	20	15	7.5
84 ± 5%	350 ± 10%	28 ± 7.5%	25	25	20	—	—

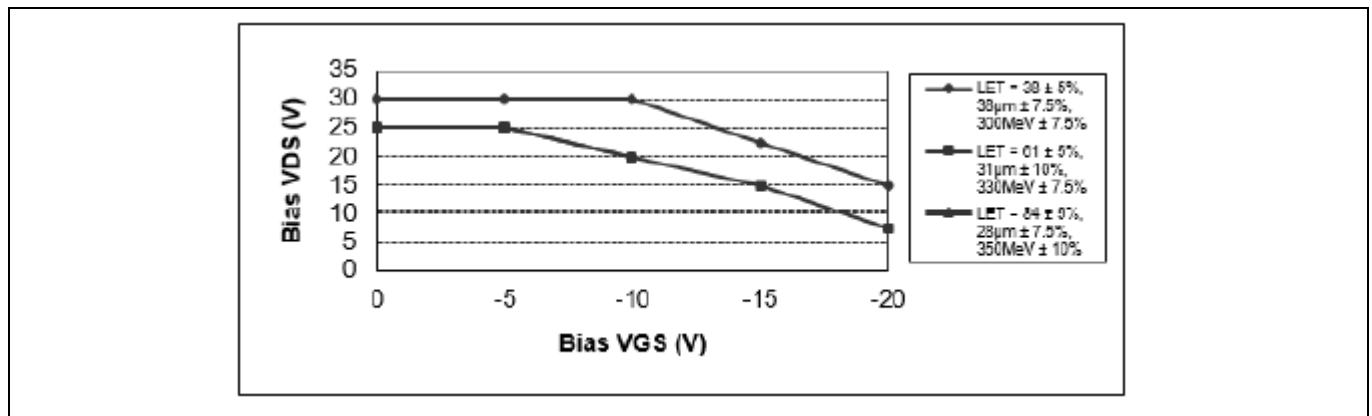


Figure 1 Typical Single Event Effect, Safe Operating Area

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Radiation Hardened Power MOSFET Surface Mount (SMD-0.5)

Electrical Characteristics Curves (Pre-irradiation)

3 Electrical Characteristics Curves (Pre-irradiation)

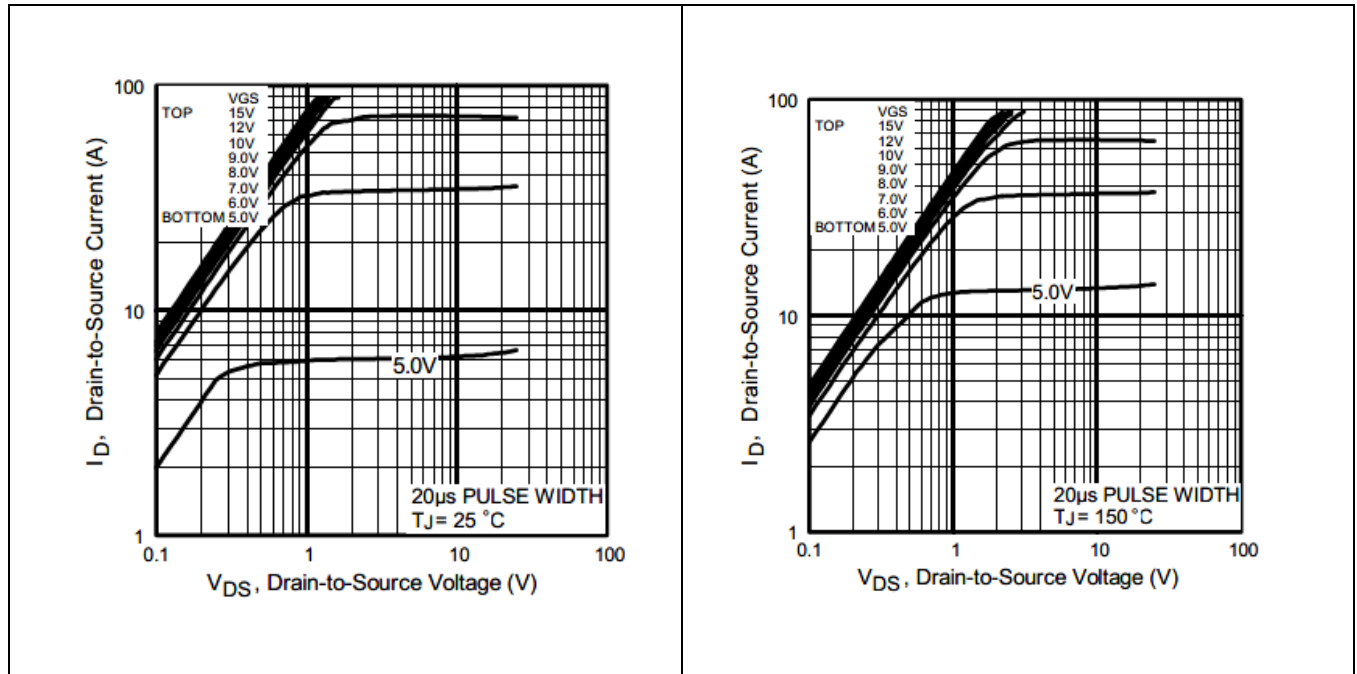


Figure 2 Typical Output Characteristics

Figure 3 Typical Output Characteristics

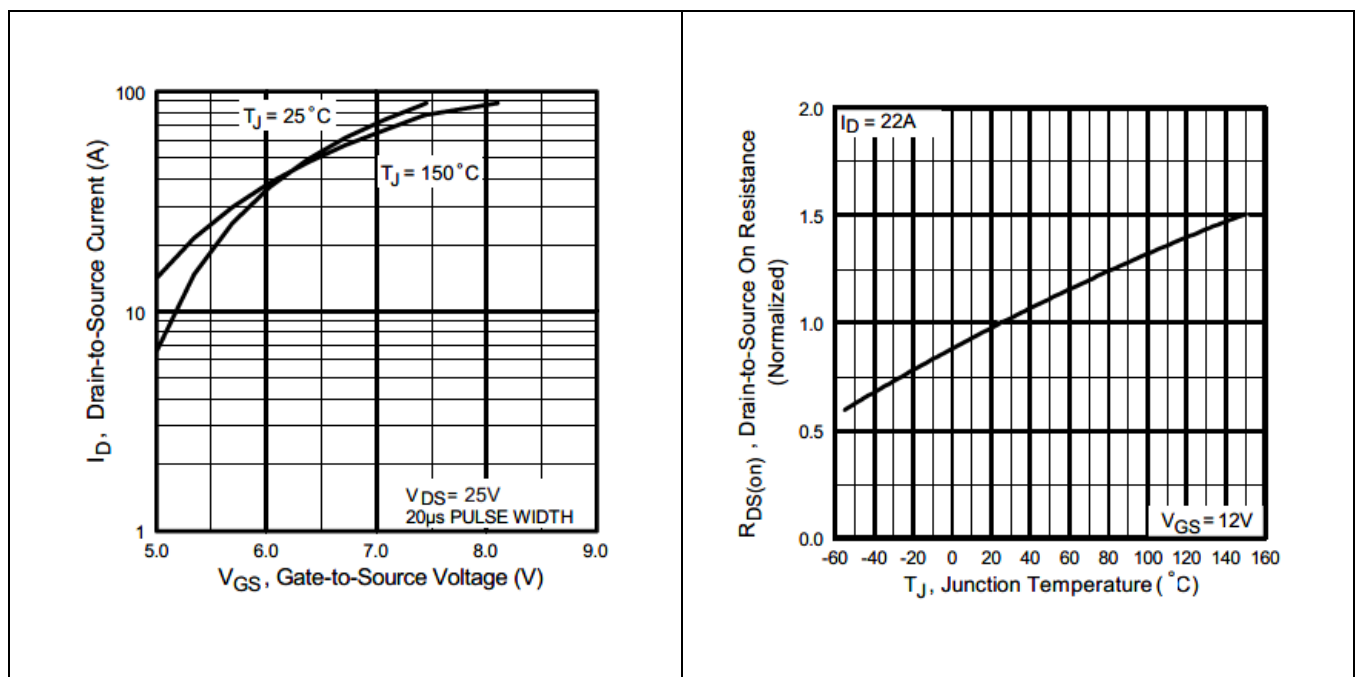


Figure 4 Typical Transfer Characteristics

Figure 5 Normalized On-Resistance Vs. Temperature

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Radiation Hardened Power MOSFET Surface Mount (SMD-0.5)

Electrical Characteristics Curves (Pre-irradiation)

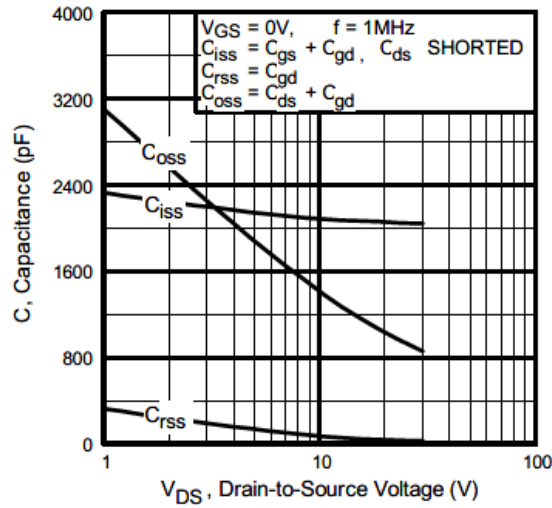


Figure 6 Typical Capacitance Vs. Drain-to-Source Voltage

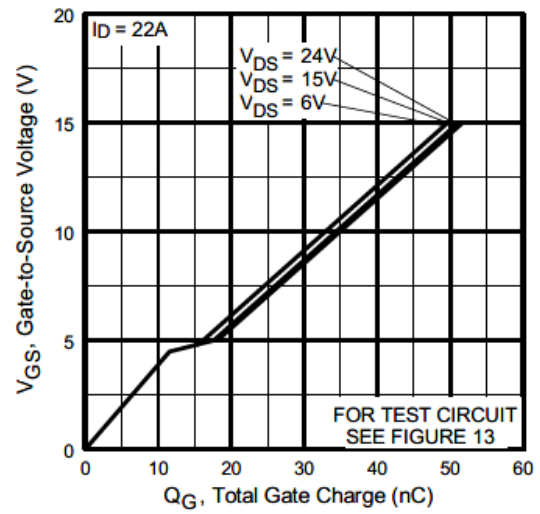


Figure 7 Typical Gate-to-Source Voltage Vs. Typical Gate Charge

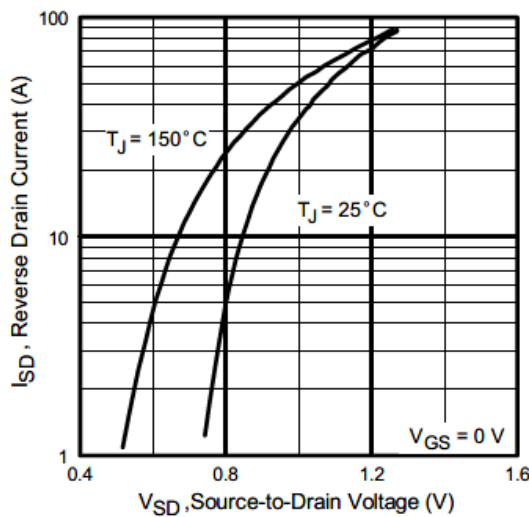


Figure 8 Typical Source-Drain Current Vs. Diode Forward Voltage

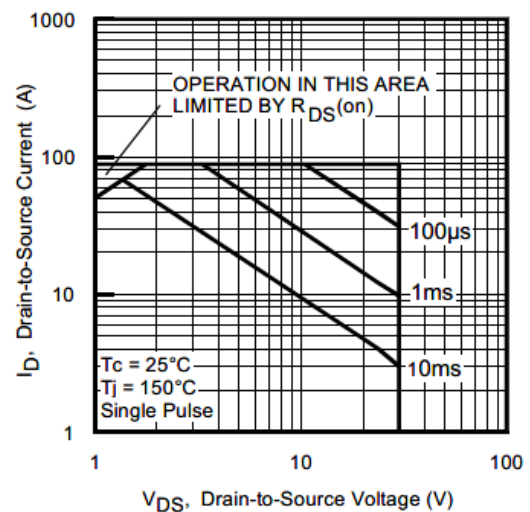


Figure 9 Maximum Safe Operating Area

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Radiation Hardened Power MOSFET Surface Mount (SMD-0.5)

Electrical Characteristics Curves (Pre-irradiation)

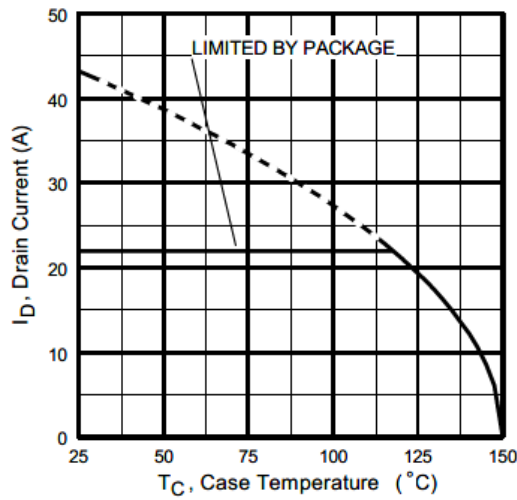


Figure 10 Maximum Drain Current Vs. Case Temperature

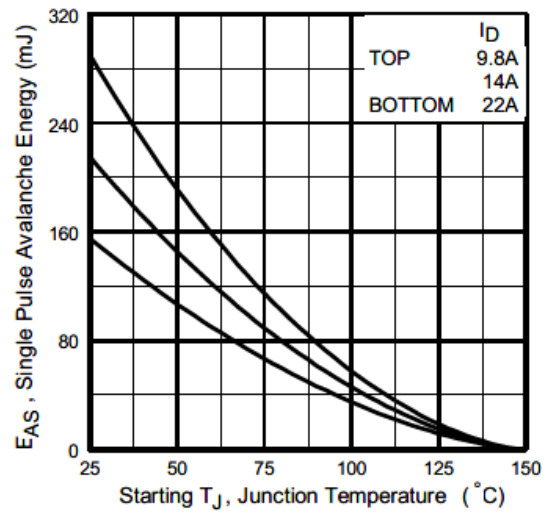


Figure 11 Maximum Avalanche Energy Vs. Junction Temperature

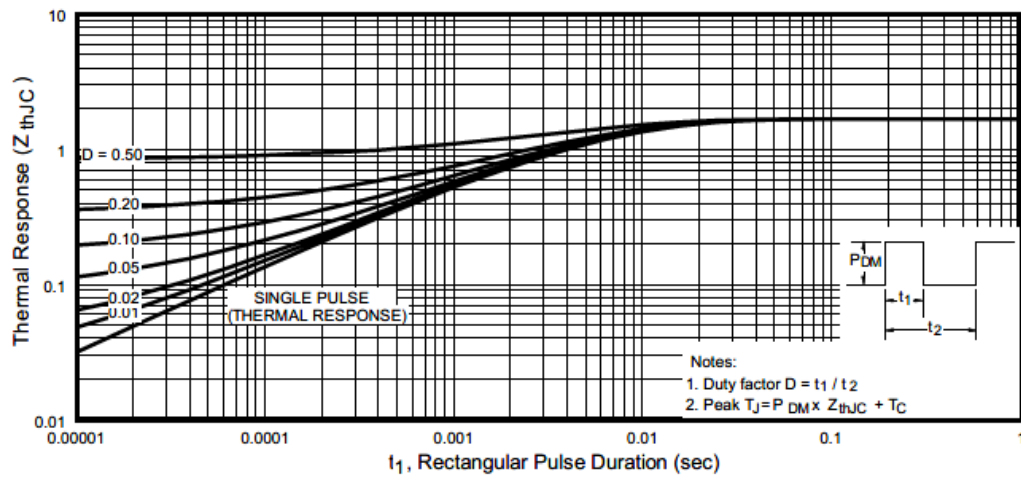


Figure 12 Maximum Effective Transient Thermal Impedance, Junction-to-Case

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Radiation Hardened Power MOSFET Surface Mount (SMD-0.5)

Test Circuits (Pre-irradiation)

4 Test Circuits (Pre-irradiation)

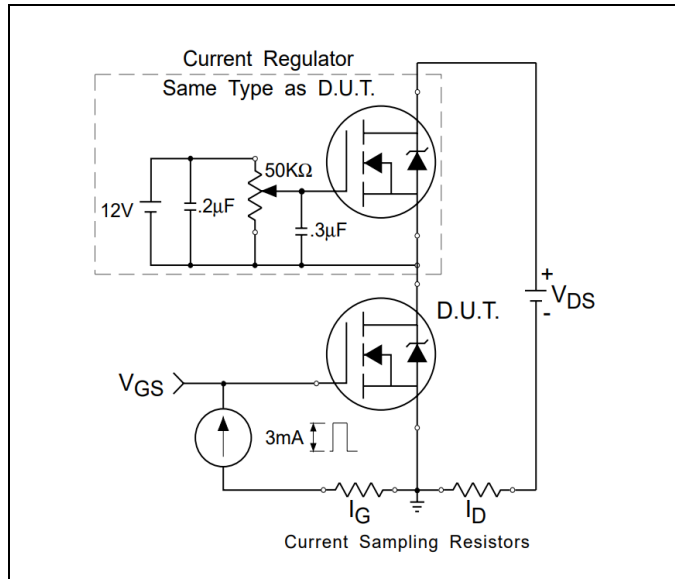


Figure 13 Gate Charge Test Circuit

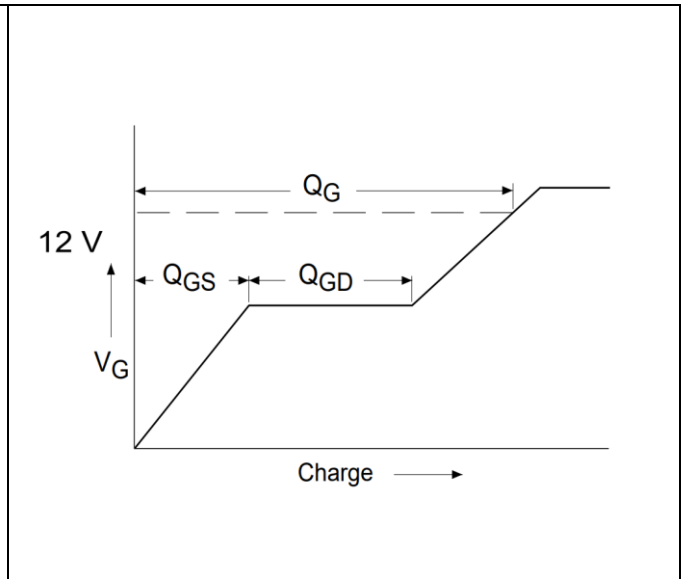


Figure 14 Gate Charge Waveform

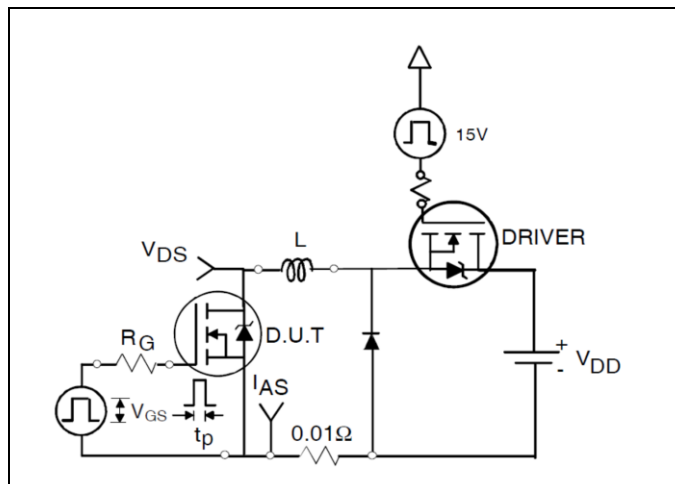


Figure 15 Unclamped Inductive Test Circuit

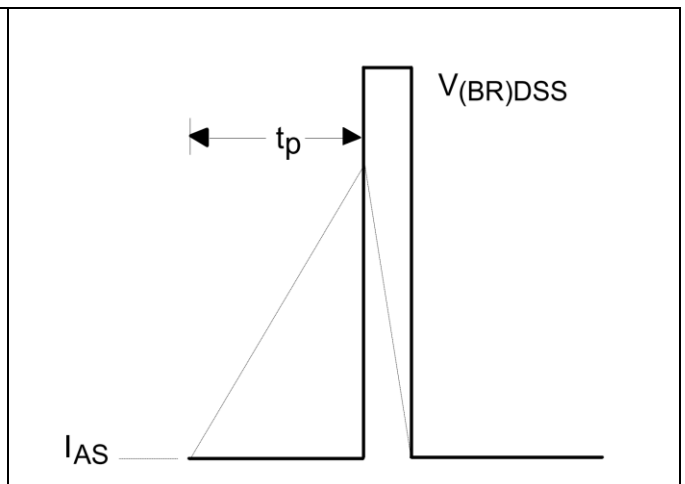


Figure 16 Unclamped Inductive Waveform

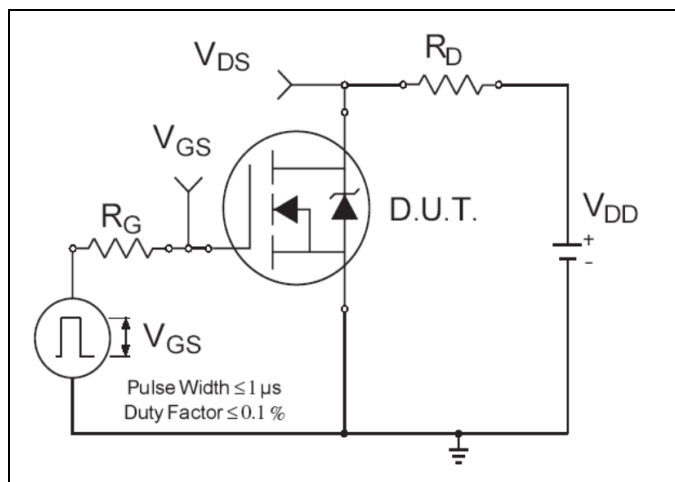


Figure 17 Switching Time Test Circuit

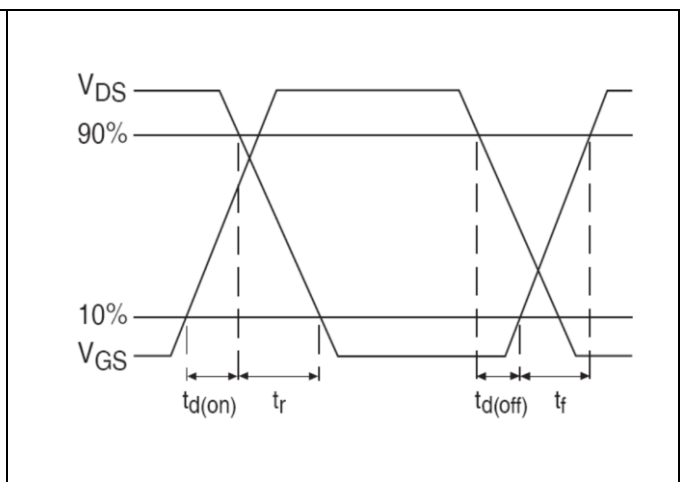


Figure 18 Switching Time Waveforms

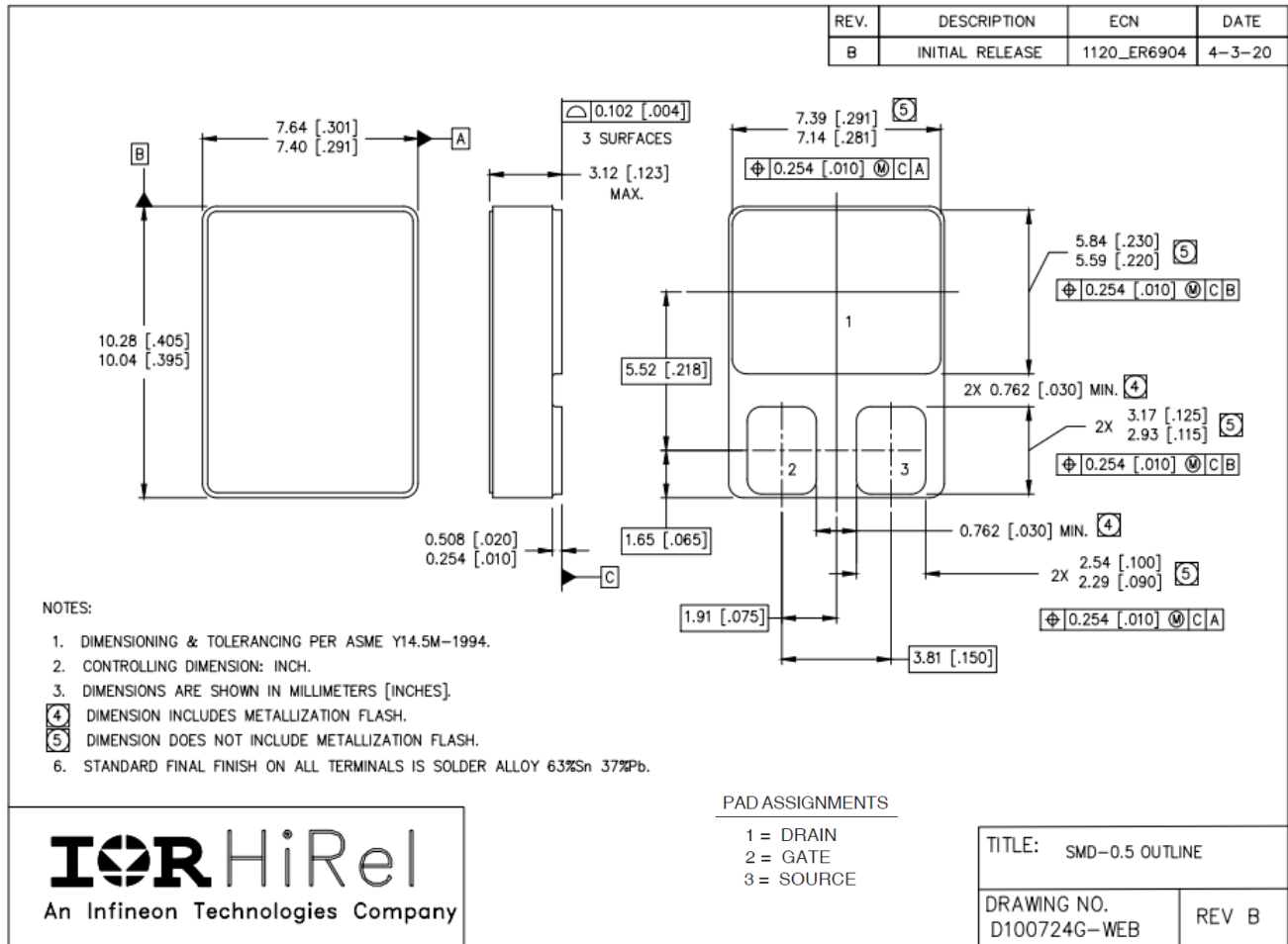
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Radiation Hardened Power MOSFET Surface Mount (SMD-0.5)

Package Outline

5 Package Outline

Note: For the most updated package outline, please see the website: [SMD-0.5](#)



IRHNJ57Z30 (JANSR2N7479U3)
Radiation Hardened Power MOSFET Surface Mount (SMD-0.5)

Revision history

Revision history

Document version	Date of release	Description of changes
	10/26/1999	Datasheet (PD-93751)
Rev A	04/11/200	Updated drawings
Rev B	07/30/2002	Updated switch time test condition
Rev C	06/16/2004	Added QPL part number
Rev D	04/25/2006	Updated 600KRad(si) to 500KRad(si)
Rev E	11/10/2020	Updated based on ECN-1120_08235
Rev F	05/25/2022	Updated based on ECN-1120_09018
Rev G	06/15/2023	Updated based on ECN-1120_09573
Rev H	12/09/2024	Updated based on ECN-1120_10110

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